

产品命名规则

CRM MOSFET Naming Rule(LV/MV MOSFET)

1	2	3	4	5	6	7	8	
CRM	K	T	L	10	130	A	Q	
								8: Special Suffix Blank= Single D= Dual same Die C= Dual different Die M= Multi-die >2 Q= Automotive, DQ/CQ/MQ for Dual Die,Multi Die A/B...Any other special use;
								7. Parameters option(use to distinguish part name when two devices have same process,package, Vds and Rdson range) A= First 1 B= Option 2 K= with ESD(First1), KB with ESD(Option2)... F= with FRD(First1), FB with FRD(Option2)... J= Unconventional Pin
								6. CP Rds(on) Typ (mohm) D9= 0.9mohm 02= 2mohm 10= 10mohm 100= 100mohm 1K5= 1.5ohm 1D7= 1.7mohm
								5. Vdss - Max (BVDSS/10) 03= 30V VDS 10= 100V VDS 15= 150V VDS
								4. Vth V= (Logic level, Vth typ <0.6V) U= Low Vth (Logic level, Vth typ 0.6~1V) L= Low Vth (Logic level, Vth typ 1~2V) H= High Vth(Vth typ >=2V)
								3. Channel/Type T= N channel Trench B= P channel Trench G= N channel SGT E= P channel SGT
								2. Package Code K TO-252-3L L SOT-23 G PDFN5x6-8L / PDFN5x6-8L-D Q PDFN3.3x3.3-8L / PDFN3.3x3.3-8L-D P SOP-8 C TO-220C-3L E TO-263-3L J SOT-23-3L
								1. Prefix CRM CRM MOSFET

CRM MOSFET Naming Rule(Super Junction)

1	2	3	4	5	6	7	
CRM	K	C	80	R380	A	Q	
							7. Special Suffix Default= Blank Q= Automotive
							6. Parameters option(use to distinguish part name when two devices have same process,package, Vds and Rdson range) A= First 1 B= Option 2 K= with ESD(First1), KB with ESD(Option2)... F= with FRD(First1), FB with FRD(Option2)...
							5. CP Rds(on) Max (mohm) 380= 380 mohm 045=45 mohm 1K5= 1.5ohm M=Muti-EPI R=Deep Trench
							4. Vdss - Max (BVDSS / 10) 80= 800V VDS 65= 650V VDS
							3. Channel /Type C= Super junction
							2. Package Code K TO-252-3L L SOT-23 G PDFN5x6-8L / PDFN5x6-8L-D Q PDFN3.3x3.3-8L / PDFN3.3x3.3-8L-D P SOP-8 C TO-220C-3L E TO-263-3L J SOT-23-3L
							1. Prefix CRM CRM MOSFET

CRM MOSFET Naming Rule(SiC MOSFET/GaN HEMT)

1	2	3	4	5	6	7	
CRM	K	S	80	P045	A	Q	
							7. Special Suffix Default= Blank Q= Automotive
							6. Parameters option(use to distinguish part name when two devices have same process,package, Vds and Rdson range) A= First 1 B= Option 2 K= with ESD(First1), KB with ESD(Option2)... F= with FRD(First1), FB with FRD(Option2)...
							5. CP Rds(on) Typ (mohm) 380= 380 mohm 045= 45 mohm 1K5= 1.5ohm P= SiC E= GaN E mode D= GaN D mode
							4. Vdss - Max (BVDSS / 10) 80= 800V VDS 65= 650V VDS
							3. Channel /Type S= SiC MOSFET H= GaN HEMT
							2. Package Code K TO-252-3L L SOT-23 G PDFN5x6-8L / PDFN5x6-8L-D Q PDFN3.3x3.3-8L / PDFN3.3x3.3-8L-D P SOP-8 C TO-220C-3L E TO-263-3L J SOT-23-3L
							1. Prefix CRM CRM MOSFET

CRM MOSFET Naming Rule(Planar MOSFET)

1	2	3	4	5	6	7	
CRM	K	P	4N	65	A	Q	
							7. Special Suffix Default= Blank Q= Automotive
							6. Parameters option(use to distinguish part name when two devices have same process,package, Vds and Rdson range) A= First 1 B= Option 2
							5. Vdss - max 65=650V 100=1000V
							4. ID - max 4N= 4A NMOS 10N= 10A NMOS 10P= 10A PMOS
							3. Channel /Type P= Planar MOSFET
							2. Package Code K TO-252-3L L SOT-23 G PDFN5x6-8L / PDFN5x6-8L-D Q PDFN3.3x3.3-8L / PDFN3.3x3.3-8L-D P SOP-8 C TO-220C-3L E TO-263-3L J SOT-23-3L
							1. Prefix CRM CRM MOSFET

CRM IGBT Discrete Naming Rule

1	2	3	4	5	6	7	8
CRT	S	40	N	120	H	3	Q
							8.Default= Blank
							Q= Automotive
							7.Option
							Generation
							6. Frequency
							RC= With FRED
							H= High Frequency: up to 100Khz
							M= Middle Frequency: up to 60Khz
							L= Low Frequency: up to 20Khz
							5. Voltage
							95= 950V
							120= 1200V
							4. N/P Type
							N= N type transistor
							P= P type transistor
							3. Current
							40= 40A
							400= 400A
							2. Package Code
							S= TO-247-3L
							SA = TO-247-4L
							E= TO-263-3L
							C= TO-220C-3L
							F= TO-220F-3L
							1. Prefix
							CRT CRM IGBT Discrete

CRM IGBT Module Naming Rule								
1	2	3	4	5	6	7	8	9
CRP	40	R	120	BS	E3	HA	E	N
								Option
								N= New Shell
								Option
								E= Enhancement(3DBC);blank=2DBC
								7.IGBT Series
								TA= Technology-SiC (Hybrid)
								EA= Engine (Motor Control)
								SA= Solar
								HA= High frequency up to 100KHz
								FA= Full speed ESS
								6.Module Housing
								62= 62 mm with Cu Base; HB2
								A3= PPack3; HE3
								B2/B3= EASY2/3 w/o Cu Base; HA2/HA3
								C2/C3= ECP2/3; HF3(Flow2 with Cu Base)
								D3= ED3 with Cu Base; HB3
								E3= EASY3 with Cu Base;HF5
								P2/P3= ECPIM2/3;HC2/HC3
								5. Module Topology
								P3= PIM Three Phase Input Rectifier
								HB= Half Bridge
								L3= 3 Level
								P4= Four Pack
								P6= Six Pack
								PM= PIM
								BS= Boost
								4. Voltage
								95= 950V
								120= 1200V
								3. Functionality
								R= Reverse Conducting
								2. Current
								40= 40A
								400= 400A
								1. Prefix
								CRP CRM IGBT Module

注：部分行业内通用料号除外，如 CRMLTL2N7002K, CRMLTU3400A 等。